



Vishay Semiconductors

RoHS COMPLIANT

HALOGEN

FREE

Thyristor High Voltage, Phase Control SCR, 25 A



3L TO-220 FullPAK

PRIMARY CHARACTERISTICS				
I _{T(AV)} 16 A				
V _{DRM} /V _{RRM}	800 V, 1200 V			
V _{TM}	1.25 V			
I _{GT}	45 mA			
TJ	-40 °C to 125 °C			
Package	3L TO-220 FullPAK			
Circuit configuration	Single SCR			

FEATURES

- · Designed and gualified for industrial level
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL pending
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-25TTS...FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter $T_A = 55 \text{ °C}$, $T_J = 125 \text{ °C}$, common heatsink of 1 °C/W	18	22	A		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	16	٨		
I _{RMS}		25	A		
V _{RRM} /V _{DRM}		800, 1200	V		
I _{TSM}		350	A		
V _T	16 A, T _J = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ		-40 to +125	°C		

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 ℃ mA			
VS-25TTS08FP-M3	800	800	10			
VS-25TTS12FP-M3	1200	1200	10			

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VS-25TTS08FP-M3, VS-25TTS12FP-M3

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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
PANAMETEN	STMDUL	TEST CONDITIONS	TYP. MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	$T_C = 51 \text{ °C}$, 180° conduction half sine wave	16		
Maximum RMS on-state current	I _{RMS}		25	^	
Maximum peak, one-cycle,	I	10 ms sine pulse, rated V _{RRM} applied	300	A	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	350		
Manufacture 124 for the size of	124	10 ms sine pulse, rated V _{RRM} applied	450	A2-	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, no voltage reapplied	630	A ² s	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1ms to 10 ms, no voltage reapplied	6300	A²√s	
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C	1.25	V	
On-state slope resistance	r _t	T 105 %	12.0	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C	1.0	V	
Maximum reverse and direct leakage current	1/1	$T_J = 25 \text{ °C}$ $V_B = \text{Rated } V_{BBM}/V_{DBM}$	0.5		
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$T_J = 125 \text{ °C}$ $V_R = \text{Rated } V_{RRM} / V_{DRM}$	10		
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 $^\circ C$	- 150	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$ 200			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 %, $V_{DRM} = R_g - k = Open$	500	V/µs	
Maximum rate of rise of turned-on current	dl/dt		150	A/µs	

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	w
Maximum average gate power	P _{G(AV)}		2.0	vv
Maximum peak positive gate current	+ I _{GM}		1.5	А
Maximum peak negative gate voltage	- V _{GM}		10	V
	I _{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	60	mA
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T_J = 25 °C	45	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20	
Maximum required DC gate		Anode supply = 6 V, resistive load, T_J = - 10 °C	2.5	
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	2.0	
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	V_{GD}	T _{.I} = 125 °C. V _{DBM} = Rated value	0.25	
Maximum DC gate current not to trigger	I _{GD}			mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	4	μs
Typical turn-off time	t _q	1J = 123 C	110	



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to 125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque minim	minimum			6 (5)	kgf ⋅ cm
	maximum			12 (10)	(lbf ⋅ in)
Marking davies				25TTS08FP	
Marking device			Case style 3L TO-220 FullPAK	25TTS12FP	



Fig. 1 - Current Rating Characteristics



Fig. 2 - Current Rating Characteristics







Fig. 4 - On-State Power Loss Characteristics

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Fig. 5 - Maximum Non-Repetitive Surge Current







Fig. 7 - On-State Voltage Drop Characteristics





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Instantaneous Gate Current (A) Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08FP-M3	50	1000	Antistatic plastic tubes		
VS-25TTS12FP-M3	50	1000	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?96155				
Part marking information	www.vishay.com/doc?95456			

Revision: 09-Jan-18 For technical questions within your region: Diode

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3L TO-220 FullPAK

DIMENSIONS in millimeters







Bottom view



Notes

- ⁽¹⁾ All dimensions are in mm
- ⁽²⁾ Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



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